

Amendments to the Specification:

Please amend paragraph [0027] as follows:

[0027] Referring to Fig. 3, crystalline form layer 16 has been exposed to plasma and a conductive reaction layer 18 comprising at least one of an elemental metal or metal rich silicide has been deposited onto plasma exposed layer 16. At least one of metal of conductive reaction layer 18 or elemental silicon of substrate 12 is diffused along columnar grain boundaries of crystalline form layer 16 effective to cause a reaction of metal of ~~conductive reaction layer 16~~ conductive reaction layer 18 with elemental silicon of substrate 12 to form a conductive metal silicide comprising contact region 20 which electrically connects ~~conductive reaction layer 16~~ conductive reaction layer 18 with substrate 12. Conductive metal silicide comprising contact region 20 preferably has a thickness from 5 Angstroms to 100 Angstroms. Conductive reaction layer 18 might be of the same, greater or lesser thickness as that of crystalline form layer 16.

Please amend paragraph [0032] as follows:

[0032] Regardless, exemplary as exemplary preferred embodiments, each of Figs. 5 and 6 depict the effective diffusing of metal with conductive reaction layer 18 along columnar grain boundaries of crystalline form layer 16/16a as being effective to form the predominate portion of metal silicide 20/20a the result of the reaction to be received beneath crystalline form layer 16/16a. Further in some exemplary preferred embodiments, the stated diffusing and reaction are effective to form all of the metal silicide from the reaction to be received either a) beneath the crystalline form layer (Fig. 5), or b) within the crystalline form layer along the columnar grain boundaries as well as beneath the crystalline form layer (Fig. 6).